

INTEGRATED CIRCUIT DEVICE CONTACT PLUGS HAVING A LINER LAYER  
THAT EXERTS COMPRESSIVE STRESS THEREON AND METHODS OF  
MANUFACTURING SAME

**Related Application**

This application claims the benefit of Korean Patent Application No. 2001-2639, filed January 17, 2001, the disclosure of which is hereby incorporated herein by reference.

**Field of the Invention**

The present invention relates generally to integrated circuit devices and manufacturing methods therefor and, more particularly, to integrated circuit device  
5 contact plugs and manufacturing methods therefor.

**Background of the Invention**

As the integration density of integrated circuit devices increases, the size of a contact plug for forming multi-layer wiring and the line width of metal wiring layers  
10 may decrease. Therefore, it may be desirable to form contact plugs using relatively low resistance metals to obtain high yield, high operating speed, and high reliability integrated circuit devices.

Contact plugs may be formed using tungsten (W) as a relatively low resistance metal. Typically, a Ti/TiN film is formed as an ohmic layer and a barrier film in the  
15 process of forming a W plug. As the critical dimension (CD) of a contact plug is reduced, however, it may be desirable to improve the relatively complicated series of processes for forming the contact plug by forming three layers of Ti, TiN, and W, respectively, and then etching the three layers. Also, when a contact plug comprises

W and a metal wiring layer also comprises W, some or all of the W contact plug may be removed by over etching when the W contact plug is exposed during a dry etching process for forming the metal wiring layer. In general, the narrower the line width of the metal wiring layer, the more susceptible the contact plug is to over etching.

- 5 Therefore, it may be desirable to use different materials for forming a contact plug and a metal wiring layer.

Polysilicon may be used to form a contact plug for use as a buried contact for electrically connecting a capacitor lower electrode of a memory device to an active region of a semiconductor substrate. When the capacitor comprises a metal-insulator-metal (MIM) structure, the polysilicon contact plug contacts the metal lower electrode of the MIM structure. When a thermal process used to form a dielectric film is performed, the polysilicon comprising the contact plug may be oxidized. Accordingly,  $\text{SiO}_2$ , which is a nonconductor, may be formed on the contact plug. Therefore, it may be desirable to use an oxidation-tolerant material when forming a contact plug for use as a buried contact.

A contact plug that comprises a TiN film may be formed by a chemical vapor deposition (CVD) process using  $\text{TiCl}_4$  and  $\text{NH}_3$  precursors (hereinafter a CVD-TiN film). Because the CVD-TiN film has generally good step coverage, it may be used to form contact plugs having a large aspect ratio. Because the CVD-TiN film has relatively high tensile stress, however, when the CVD-TiN film is deposited to a thickness more than 50 nm, cracks may be generated in the CVD-TiN film and also in an interlayer dielectric film around the CVD-TiN film. To completely fill the contact plug space with the CVD-TiN film, TiN is typically deposited to a thickness of more than half of the contact plug CD to be formed. For example, to form a TiN contact plug having a CD of 200 nm, TiN may be deposited to a thickness of more than 100 nm. Because cracks may be generated when the thickness of the CVD-TiN film is more than 50 nm, it may be difficult to use CVD-TiN film to form contact plugs having a CD greater than 100 nm.

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### **Summary of the Invention**

According to embodiments of the present invention, an integrated circuit device comprises a substrate and an insulating layer that is disposed on the substrate and has a gap or hole formed therein. A liner layer that exhibits compressive stress

characteristics is disposed on the sidewalls of the insulating layer, which define the gap, and also on the substrate in the gap. A contact plug that exhibits tensile stress characteristics is disposed on the liner layer. Advantageously, the compressive stress of the liner layer may reduce the tensile stress of the contact plug. Therefore, despite  
5 the tensile stress exhibited by the contact plug, the combination of the liner layer with the contact plug may inhibit the formation of cracks in the contact plug and/or in an interlayer dielectric film around the contact plug regardless of the thickness of the contact plug.

10 In other embodiments, the liner layer and the contact plug comprise titanium nitride (TiN).

In still other embodiments, the liner layer is formed using one of the following methods: ionized physical vapor deposition (IPVD), metal organic chemical vapor deposition (MOCVD), metal organic atomic layer deposition (MOALD), sputtering, and collimator sputtering.

15 In further embodiments, the contact plug is formed using one of the following methods: chemical vapor deposition (CVD), atomic layer deposition (ALD), MOCVD, and MOALD.

In further embodiments, an ohmic layer is disposed between the liner layer and the sidewalls of the insulating layer, and between the liner layer and the substrate.

20 In still further embodiments, a wiring layer is disposed on an upper surface of the contact plug opposite the substrate.

In still further embodiments, a capacitor is disposed on an upper surface of the contact plug opposite the substrate.

## 25 **Brief Description of the Drawings**

Other features of the present invention will be more readily understood from the following detailed description of specific embodiments thereof when read in conjunction with the accompanying drawings, in which:

30 **FIGS. 1, 2, 3A - 3E, and 4A - 4D** are cross sectional views that illustrate integrated circuit device contact plugs having a liner layer that exerts compressive stress thereon and methods of manufacturing same in accordance with embodiments of the present invention.

### Detailed Description of Preferred Embodiments

While the invention is susceptible to various modifications and alternative forms, specific embodiments thereof are shown by way of example in the drawings and will herein be described in detail. It should be understood, however, that there is  
5 no intent to limit the invention to the particular forms disclosed, but on the contrary, the invention is to cover all modifications, equivalents, and alternatives falling within the spirit and scope of the invention as defined by the claims. Like numbers refer to like elements throughout the description of the figures. In the figures, the dimensions of layers and regions are exaggerated for clarity. It will also be understood that when  
10 an element, such as a layer, region, or substrate, is referred to as being "on" another element, it can be directly on the other element or intervening elements may be present. In contrast, when an element, such as a layer, region, or substrate, is referred to as being "directly on" another element, there are no intervening elements present.

Referring now to **FIG. 1**, a contact plug **10**, according to embodiments of the  
15 present invention, is formed so as to pass through an insulating film **22** interposed between a conductive region (not shown) on a semiconductor substrate **12** and a metal wiring layer **32** on the insulating film **22** to electrically connect the conductive region to the metal wiring layer **32**. The metal wiring layer **32** may comprise, for example, a W wiring layer and/or an Al wiring layer, and may be part of a multi-layer wiring  
20 structure.

The contact plug **10** comprises a TiN plug **18**, which exhibits tensile stress characteristics and a TiN liner **16**, which exhibits compressive stress characteristics. A Ti ohmic layer **14** is formed between the TiN liner **16** and the insulating film **22**, and between the TiN liner **16** and the conductive region of the semiconductor  
25 substrate **12**.

The upper surface **18t** of the TiN plug **18** contacts the upper wiring layer **32**, and the sidewall **18s** and the bottom surface **18b** of the TiN plug **18** contact the TiN liner **16**. In other words, the TiN liner **16** surrounds the sidewall **18s** and the bottom surface **18b** of the TiN plug **18**. In some embodiments, the TiN plug **18** may be  
30 formed so that the width of the upper surface **18t** is approximately equal to the width of the bottom surface **18b**. In other embodiments, the TiN plug **18** may be formed so that the width of the upper surface **18t** is greater than the width of the bottom surface

18b. The Ti ohmic layer 14 contacts the TiN liner 16 on the opposite side of the TiN plug 18.

The TiN plug 18 may comprise a TiN film formed using chemical vapor deposition (CVD), atomic layer deposition (ALD), metal organic CVD (MOCVD), or metal organic ALD (MOALD). The TiN liner 16 may comprise a TiN film formed using ionized physical vapor deposition (IPVD), MOCVD, MOALD, sputtering, or collimator sputtering.

The TiN liner 16 may inhibit the generation of cracks in the contact plug 10 and the insulating film 22 around the contact plug 10 by buffering the tensile stress of the TiN plug 18. The TiN liner 16 may have an amorphous crystal structure. To facilitate formation of an amorphous crystal structure, the TiN liner 16 may be formed using IPVD. A TiN film obtained using MOCVD or MOALD may exhibit tensile stress characteristics or compressive stress characteristics based on process variables used in the deposition process, such as the process gas mass flow and the deposition temperature. Therefore, a TiN film may be formed that exhibits tensile stress characteristics or compressive stress characteristics by appropriately controlling deposition process variables.

Referring now to FIG. 2, a contact plug 50, according to other embodiments of the present invention, is used as a buried contact to electrically connect a lower electrode 82, which comprises part of an integrated circuit memory device capacitor 80, to an active region (not shown) on an integrated circuit substrate 40. If the capacitor 80 comprises a metal-insulator-metal (MIM) structure, then the lower electrode 82 may comprise a single film formed of a metal, such as W, Pt, Ru, and/or Ir, a conductive metal nitride, such as TiN, TaN, and/or WN, and/or a conductive metal oxide, such as RuO<sub>2</sub> and IrO<sub>2</sub>.

A TiN plug 58, a TiN liner 56, and a Ti ohmic layer 54, which comprise the contact plug 50, may have the same structures as the TiN plug 18, the TiN liner 16, and the Ti ohmic layer 14, respectively, which have been described above with reference to FIG. 1.

FIGS. 3A through 3E are cross-sectional views that illustrate methods of manufacturing integrated circuit device contact plugs and integrated circuit devices formed thereby in accordance with embodiments of the present invention.

Referring now to **FIG. 3A**, an insulating layer **110** is formed on a semiconductor substrate **100**. The insulating layer **110** is etched to define a contact hole or gap **H1** therein, which exposes a conductive region **102** in the semiconductor substrate **100**.

5 Referring now to **FIG. 3B**, an ohmic layer **120** is formed on the entire surface of the structure of **FIG. 3A** to a thickness of about 70 Å- 100 Å so as to cover the inside wall of the contact hole **H1**. The ohmic layer **120** may comprise a Ti film formed using plasma enhanced CVD (PECVD), collimator sputtering, IPVD, or physical vapor deposition (PVD).

10 Referring now to **FIG. 3C**, a TiN liner **122**, which exhibits compressive stress characteristics, is formed on the ohmic layer **120** to a thickness of about 200 Å - 500 Å. The TiN liner **122** may be formed by depositing TiN using IPVD, MOCVD, MOALD, sputtering, or collimator sputtering. If the TiN liner **122** is formed by depositing TiN using IPVD, then the TiN liner **122** may have an amorphous crystal structure.

15 Referring now to **FIG. 3D**, a TiN film **124**, which exhibits tensile stress characteristics, is formed on the structure of **FIG. 3C** so as to completely fill the contact hole **H1**. The TiN film **124** may be formed by depositing TiN using CVD, ALD, MOCVD, or MOALD. Advantageously, forming the TiN film **124** using the  
20 aforementioned methods may allow the TiN film **124** to exhibit relatively good step coverage in filling the contact hole **H1**.

In some embodiments, the TiN film **124** may be formed using CVD or ALD in which  $\text{TiCl}_4$  and  $\text{NH}_3$  are used as precursors. In other embodiments, the TiN film **124** may be formed using MOCVD or MOALD in which a precursor, such as tetrakis di-  
25 methyl amido titanium (TDMAT) and tetrakis di-ethyl amido titanium (TDEAT) together with  $\text{NH}_3$  or  $\text{H}_2$ , may be used.

In general, because TiN films formed using CVD or ALD exhibit relatively large tensile stress characteristics, cracks may be generated when the thickness of the TiN film is greater than 50 nm. A TiN film formed using MOCVD or MOALD may  
30 exhibit tensile stress characteristics by appropriately controlling deposition process variables, such as the process gas mass flow and the deposition temperature. Even though the TiN film **124** may exhibit tensile stress characteristics, this tension may be

reduced due to the compressive stress exhibited by the TiN liner 122, which is formed before forming the TiN film 124 as described above with reference to FIG. 3C. If the TiN liner 122 is formed using IPVD, then the TiN liner 122 may have an amorphous crystal structure and the fine structure and the crystal direction of TiN deposited on the TiN liner 122 may be changed. The TiN liner 122 may, therefore, affect the fine structure and the crystal direction of the TiN film 124 formed thereon. As a result, the compressive stress exhibited by the TiN liner 122 may reduce the tensile stress exhibited by the TiN film 124. Thus, the combination of the TiN liner 122 with the TiN film 124 may inhibit the formation of cracks in the TiN film 124 and/or the insulating film 110.

TiN films formed using MOCVD or MOALD in which metallo-organics are used generally exhibit relatively small stress characteristics on the order of about  $10^9$ . The compressive and/or tensile stress characteristics of a TiN film may be adjusted based on the deposition process control variables. The TiN liner 122 and the TiN film 124 may be formed to have desired stress characteristics using MOCVD and/or MOALD after forming the ohmic layer 120 in the contact hole H1.

Referring now to FIG. 3E, the insulating layer pattern 110 is exposed by planarizing the structure of FIG. 3D by performing, for example, chemical mechanical polishing (CMP) or etching. A contact plug 130 may be formed, which comprises the ohmic layer 120, the TiN liner 122, and a TiN plug 124a, inside the contact hole H1.

As described above with reference to FIGS. 3A through 3E, the TiN liner 122 may be formed using IPVD. When a TiN film is formed in a contact hole using IPVD, a void may be formed in the resulting contact plug after the contact hole is filled. Exemplary methods for inhibiting the formation of a void, in accordance with embodiments of the present invention, will now be described.

FIGS. 4A through 4D are cross-sectional views that illustrate methods of manufacturing integrated circuit device contact plugs and integrated circuit devices formed thereby in accordance with further embodiments of the present invention.

Referring now to FIG. 4A, an insulating film pattern 210 is formed on a semiconductor substrate 200. The insulating film pattern 210 is anisotropically etched to define a contact hole or gap therein, which exposes a conductive region 202 in the

semiconductor substrate **200**. The width  $W_n$  at the entrance of the hole is approximately equal to the width  $W_B$  at the bottom of the hole where the conductive region **202** is exposed.

Referring now to **FIG. 4B**, a second insulating film pattern **210a** is formed by isotropically etching a portion around the entrance of the insulating film pattern **210** to define a contact hole **H2** in which the width  $W_{12}$  at the entrance of the contact hole **H2** is greater than the previous width  $W_n$  of the hole entrance, and is also greater than the width  $W_B$  at the bottom of the contact hole. The isotopic etching may be performed using wet etching and a photoresist pattern as an etching mask.

Referring now to **FIG. 4C**, an ohmic layer **220**, a TiN liner **222** that exhibits compressive stress characteristics, and a TiN film **224** that exhibits tensile stress characteristics are formed on the structure of **FIG. 4B** as described above with reference to **FIGS. 3B** through **3D**. Because the entrance to the contact hole **H2** has a relatively large width  $W_{12}$ , there may be a reduced probability that the ohmic layer **220**, the TiN liner **222**, and the TiN film **224**, which are formed in the contact hole **H2** will contain a void. The compressive stress exhibited by the TiN liner **222** may reduce the tensile stress exhibited by the TiN film **224**. Thus, the combination of the TiN liner **222** with the TiN film **224** may inhibit the formation of cracks in the TiN film **224** and/or the second insulating film pattern **210a**.

Referring now to **FIG. 4D**, the upper surface **210t** of a planarized second insulating film pattern **210b** is exposed by planarizing the structure of **FIG. 4C** by performing, for example, chemical mechanical polishing (CMP) or etching. A contact plug **230** may be formed, which comprises the ohmic layer **220**, the TiN liner **222**, and a TiN plug **224a**, inside the contact hole **H2**. Advantageously, according to embodiments of the present invention, the contact plug **230** may have a reduced susceptibility to cracking and the formation of voids therein.

Table 1 contains experimental results, which were obtained by estimating the stress of various kinds of TiN films and which can be used for forming contact plugs according to embodiments of the present invention. The results of Table 1 were obtained by forming TiN films on a plurality of silicon substrates to a thickness of 1000 Å and then measuring the stresses on these films.



Table 1

Deposition method for forming TiN film	Stress (dyne/cm <sup>2</sup> )
Sputtering method	-1.6E10 (compressive stress)
Collimator sputtering method	-2.5E10 (compressive stress)
IPVD (SIP)	-3.3E10 (compressive stress)
IPVD (IMP)	-4.3E10 (compressive stress)
CVD	+1E10 through +3E10 (tensile stress)
ALD	+1E10 through +3E10 (tensile stress)

In Table 1, IPVD (SIP) means the IPVD in a self-ionized plasma (SIP), and IPVD (IMP) means IPVD in an ionized metal plasma (IMP). The results of Table 1, show TiN films formed by sputtering, collimator sputtering, IPVD (SIP), and IPVD (IMP), exhibit compressive stress characteristics. TiN films formed by CVD and ALD, in which TiCl<sub>4</sub> is used as the precursor, exhibit relatively high tensile stress characteristics on the order of 10<sup>10</sup> dynes/cm<sup>2</sup>.

Based on the above results, if a TiN film is formed to a thickness of more than 50 nm by CVD or ALD, then cracks generated in the TiN film and/or an interlayer dielectric film surrounding the TiN film may be caused by the relatively high tensile stress characteristics of the TiN film. According to embodiments of the present invention, when forming a TiN contact plug, a TiN liner that exhibits compressive stress may be formed around a TiN plug to reduce the tensile stress in the TiN contact plug. Thus, through use of a TiN liner that exhibits compressive stress, it may be possible to reduce the susceptibility of a TiN film formed by CVD or ALD to cracks regardless of the thickness of the TiN film. A TiN liner formed using IPVD may exhibit compressive stress characteristics and may have an amorphous crystal structure. Moreover, the fine structure and the crystal direction of TiN deposited on the TiN liner may be changed. It has been confirmed through experiments and observations using a scanning electron microscope (SEM) that a TiN film that is affected by the crystal structure of an underlayer as discussed above may be less likely to crack.

Embodiments of the present invention have been described in the context of forming a contact plug by forming a TiN plug that exhibits tensile stress characteristics after forming a TiN liner that exhibits compressive stress characteristics. It will be understood, however, that the present invention is not limited to these exemplary embodiments. For example, in other embodiments, a contact plug may be formed by using a multi-step process of repeatedly forming a TiN film that exhibits compressive stress characteristics and forming a TiN film that exhibits tensile stress characteristics so as to overlap the TiN film having the compressive stress characteristics and the TiN film having the tensile stress characteristics.

According to embodiments of the present invention, a contact plug may be formed by forming an ohmic layer, forming a TiN liner that exhibits compressive stress characteristics on the ohmic layer, and then forming a TiN plug that exhibits tensile stress characteristics on the TiN liner. Advantageously, the compressive stress of the TiN liner may reduce the tensile stress of the TiN plug. In particular, if the TiN liner is formed using IPVD, then the TiN liner may have an amorphous crystal structure. Moreover, the fine structure and the crystal direction of TiN deposited on the TiN liner may be changed. Therefore, despite the relatively large tensile stress exhibited by the TiN film, the combination of the TiN liner with the TiN film may inhibit the formation of cracks in the TiN film and/or in an interlayer dielectric film around the TiN film regardless of the thickness of the TiN film.

In concluding the detailed description, it should be noted that many variations and modifications can be made to the preferred embodiments without substantially departing from the principles of the present invention. All such variations and modifications are intended to be included herein within the scope of the present invention, as set forth in the following claims.